



US 20240237389A1

(19) **United States**

(12) **Patent Application Publication**  
**FENG et al.**

(10) **Pub. No.: US 2024/0237389 A1**

(43) **Pub. Date: Jul. 11, 2024**

(54) **QUANTUM DOT LIGHT EMITTING DIODE,  
MANUFACTURING METHOD THEREOF  
AND DISPLAY PANEL**

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(21) Appl. No.: **18/617,524**

(22) Filed: **Mar. 26, 2024**

**Related U.S. Application Data**

(63) Continuation of application No. 17/458,782, filed on  
Aug. 27, 2021, now Pat. No. 11,974,448.

**Foreign Application Priority Data**

Oct. 16, 2020 (CN) ..... 202011110885.2

**Publication Classification**

(51) **Int. Cl.**

**H10K 50/16** (2023.01)

**H10K 50/115** (2023.01)

**H10K 71/00** (2023.01)

**H10K 102/00** (2023.01)

(52) **U.S. Cl.**

CPC ..... **H10K 50/166** (2023.02); **H10K 50/115**

(2023.02); **H10K 71/00** (2023.02); **H10K**

**2102/00** (2023.02); **H10K 2102/351** (2023.02)

(57)

**ABSTRACT**

The present disclosure provides a quantum dot light emitting diode, including: a first electrode, a second electrode, a quantum dot light emitting layer between the first electrode and the second electrode, at least one electron transport layer between the quantum dot light emitting layer and the first electrode, and an electron contribution layer between the electron transport layer of the at least one electron transport layer closest to the first electrode and the quantum dot light emitting layer; a material of the electron contribution layer includes a metal material. The embodiment of the present disclosure also provides a method for manufacturing the quantum dot light emitting diode and a display panel.

